


 Cite this: *Phys. Chem. Chem. Phys.*,
2023, 25, 25055

Correction: Lone pair driven anisotropy in antimony chalcogenide semiconductors

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DOI: 10.1039/d3cp90185h

 Correction for 'Lone pair driven anisotropy in antimony chalcogenide semiconductors' by Xinwei Wang *et al.*, *Phys. Chem. Chem. Phys.*, 2022, 24, 7195–7202, <https://doi.org/10.1039/D1CP05373F>.

rsc.li/pccp

The authors regret that Fig. 5(b) was incorrect in the original manuscript due to a minor error in the code used for calculating the orientation-dependent radiative limit to photovoltaic conversion efficiency. The corrected figure is shown here. The optical absorption spectra of Sb_2S_3 and Sb_2Se_3 result in a weak orientation-dependent radiative limit of conversion efficiencies. When the film thickness is 500 nm, the difference between the maximum and minimum efficiencies along different directions is 1.31% and 2.40% for Sb_2S_3 and Sb_2Se_3 , respectively. The authors note that the correction of Fig. 5(b) does not change the central conclusions of the paper.

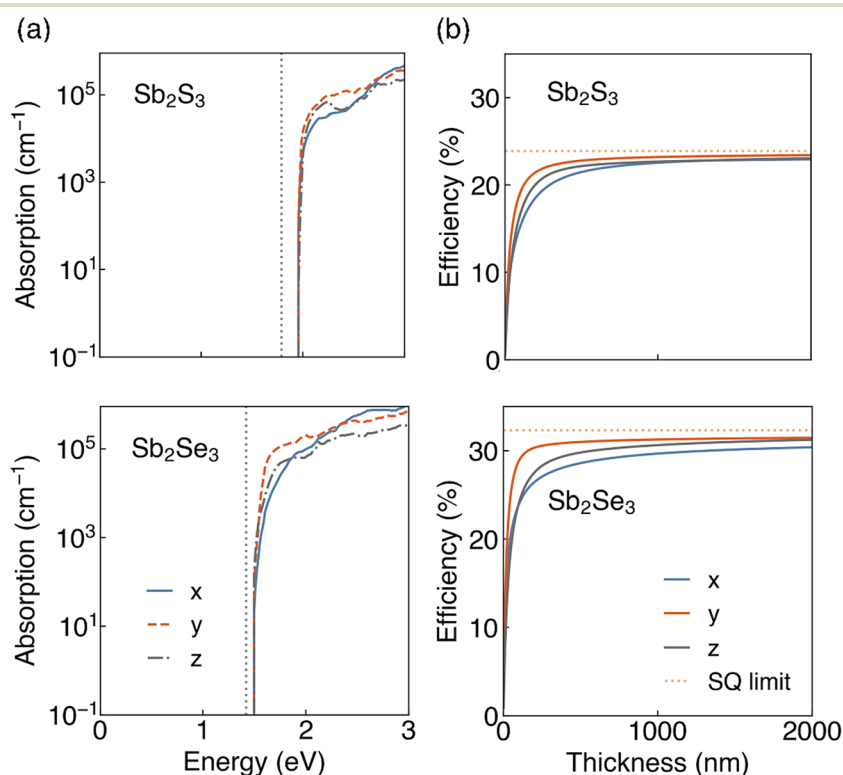


Fig. 5 (a) Calculated optical absorption spectra of Sb_2S_3 and Sb_2Se_3 arising from direct valence to conduction band transitions. The fundamental band gaps are shown in grey dotted lines. (b) Thickness-dependent maximum efficiencies based on the radiative limit of Sb_2S_3 and Sb_2Se_3 . x, y and z refer to the direction of the electric polarisation vector of light.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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